
2SK1668

Silicon N-Channel MOS FET

HITACHI

ADE-208-1309 (Z)
1st. Edition
Mar. 2001

Application

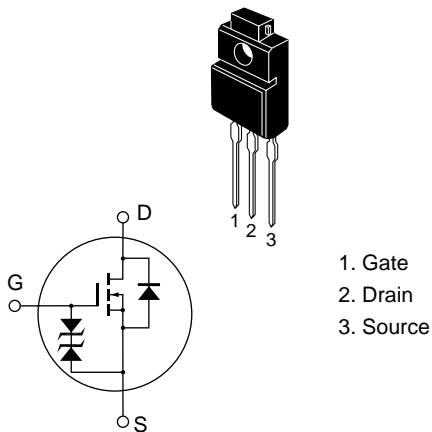
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC – DC converter

Outline

TO-220FM



2SK1668

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	250	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D	7	A
Drain peak current	$I_{D(pulse)}^{*1}$	28	A
Body to drain diode reverse drain current	I_{DR}	7	A
Channel dissipation	Pch^{*2}	30	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1. PW 10 μs, duty cycle 1%
2. Value at T_c = 25°C

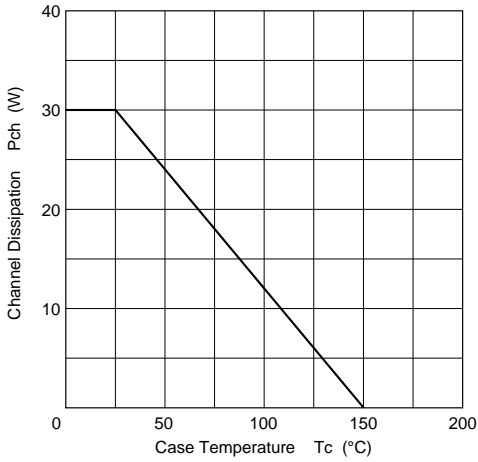
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	250	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	μA	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.4	0.55		$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	3.0	5.0	—	S	$I_D = 4 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	690	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	C_{oss}	—	265	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	45	—	pF	
Turn-on delay time	$t_{d(on)}$	—	13	—	ns	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t_r	—	55	—	ns	$R_L = 7.5$
Turn-off delay time	$t_{d(off)}$	—	65	—	ns	
Fall time	t_f	—	37	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 7 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	180	—	ns	$I_F = 7 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

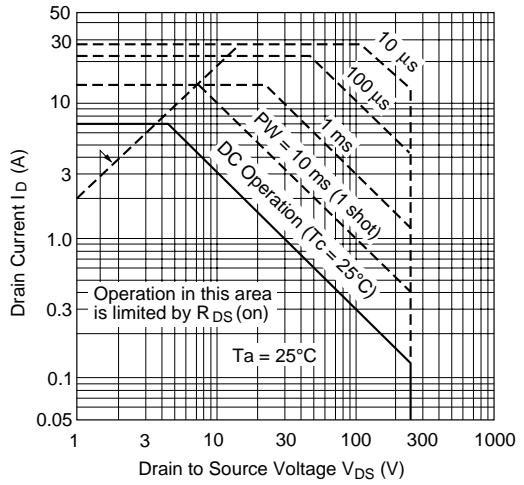
Note 1. Pulse test

See characteristic curves of 2SK1667.

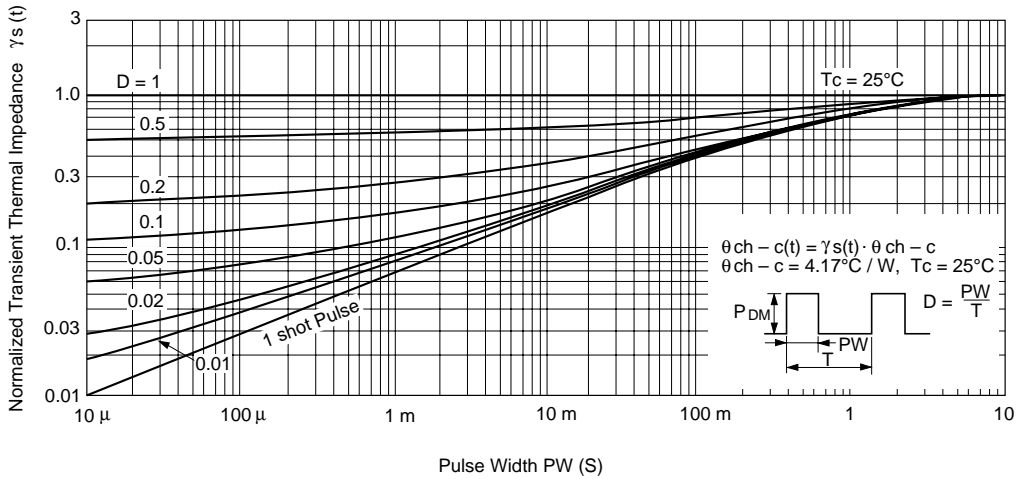
Power vs. Temperature Derating



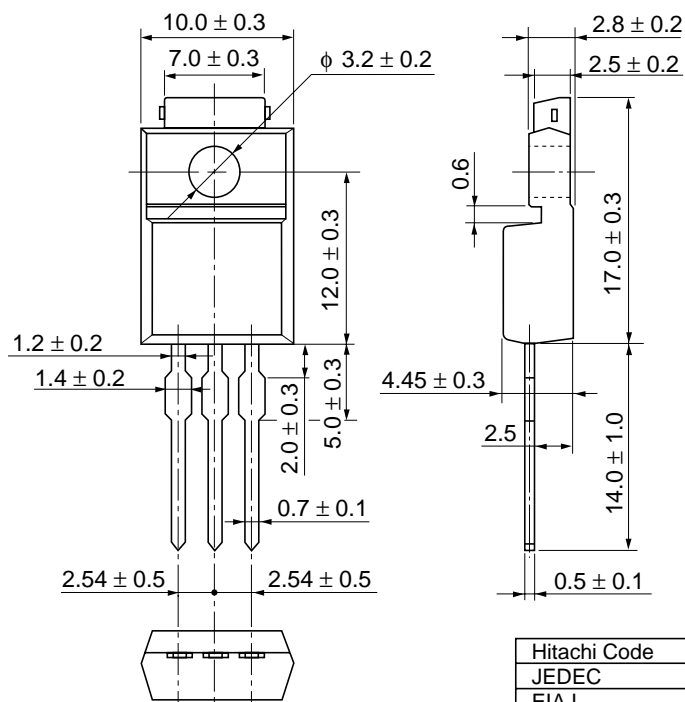
Maximum Safe Operation Area



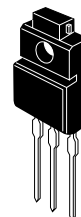
Normalized Transient Thermal Impedance vs. Pulse Width



Package Dimensions



As of January, 2001
Unit: mm



Hitachi Code	TO-220FM
JEDEC	—
EIAJ	Conforms
Mass (reference value)	1.8 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
 Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
 Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
 Europe : <http://www.hitachi-eu.com/hel/ecg>
 Asia : <http://sicapac.hitachi-asia.com>
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For further information write to:

Hitachi Semiconductor
 (America) Inc.
 179 East Tasman Drive,
 San Jose, CA 95134
 Tel: <1> (408) 433-1990
 Fax: <1> (408) 433-0223

Hitachi Europe GmbH
 Electronic Components Group
 Dornacher Straße 3
 D-85622 Feldkirchen, Munich
 Germany
 Tel: <49> (89) 9 9180-0
 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
 Electronic Components Group.
 Whitebrook Park
 Lower Cookham Road
 Maidenhead
 Berkshire SL6 8YA, United Kingdom
 Tel: <44> (1628) 585000
 Fax: <44> (1628) 585160

Hitachi Asia Ltd.
 Hitachi Tower
 16 Collyer Quay #20-00,
 Singapore 049318
 Tel : <65>-538-6533/538-8577
 Fax : <65>-538-6933/538-3877
 URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
 (Taipei Branch Office)
 4/F, No. 167, Tun Hwa North Road,
 Hung-Kuo Building,
 Taipei (105), Taiwan
 Tel : <886>-(2)-2718-3666
 Fax : <886>-(2)-2718-8180
 Telex : 23222 HAS-TP
 URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
 Group III (Electronic Components)
 7/F., North Tower,
 World Finance Centre,
 Harbour City, Canton Road
 Tsim Sha Tsui, Kowloon,
 Hong Kong
 Tel : <852>-(2)-735-9218
 Fax : <852>-(2)-730-0281
 URL : <http://www.hitachi.com.hk>

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